

NTMS4107N

Power MOSFET

30 V, 18 A, Single N-Channel, SO-8

Features

- Ultra Low $R_{DS(on)}$ (at 4.5 V_{GS}), Low Gate Resistance and Low Q_G
- Optimized for Low Side Synchronous Applications
- High Speed Switching Capability
- Pb-Free Package is Available

Applications

- Notebook Computer Vcore Applications
- Network Applications
- DC-DC Converters

MAXIMUM RATINGS ($T_J = 25^\circ\text{C}$ unless otherwise noted)

Rating		Symbol	Value	Unit	
Drain-to-Source Voltage		V_{DSS}	30	V	
Gate-to-Source Voltage		V_{GS}	± 20	V	
Continuous Drain Current (Note 1)	Steady State	$T_A = 25^\circ\text{C}$	I_D	15	A
			$T_A = 85^\circ\text{C}$	11	
	$t \leq 10\text{ s}$	$T_A = 25^\circ\text{C}$	18		
Power Dissipation (Note 1)	Steady State	$T_A = 25^\circ\text{C}$	P_D	1.67	W
			$t \leq 10\text{ s}$	2.5	
Continuous Drain Current (Note 2)	Steady State	$T_A = 25^\circ\text{C}$	I_D	11	A
		$T_A = 85^\circ\text{C}$	8.0		
		$T_A = 25^\circ\text{C}$	P_D	0.93	
Power Dissipation (Note 2)					
Pulsed Drain Current	$t_p = 10\ \mu\text{s}$	I_{DM}	56	A	
Operating Junction and Storage Temperature		T_J, T_{stg}	-55 to 150	$^\circ\text{C}$	
Continuous Source Current (Body Diode)		I_S	3.0	A	
Single Pulse Drain-to-Source Avalanche Energy ($V_{DD} = 30\text{ V}$, $V_{GS} = 10\text{ V}$, $I_{PK} = 32\text{ A}$, $L = 1\text{ mH}$, $R_G = 25\ \Omega$)		E_{AS}	512	mJ	
Lead Temperature for Soldering Purposes (1/8" from case for 10 s)		T_L	260	$^\circ\text{C}$	

THERMAL RESISTANCE RATINGS

Rating	Symbol	Max	Unit
Junction-to-Ambient - Steady State (Note 1)	$R_{\theta JA}$	75	$^\circ\text{C}/\text{W}$
Junction-to-Ambient - $t \leq 10\text{ s}$ (Note 1)	$R_{\theta JA}$	50	
Junction-to-Ambient - Steady State (Note 2)	$R_{\theta JA}$	135	

Maximum ratings are those values beyond which device damage can occur. Maximum ratings applied to the device are individual stress limit values (not normal operating conditions) and are not valid simultaneously. If these limits are exceeded, device functional operation is not implied, damage may occur and reliability may be affected.

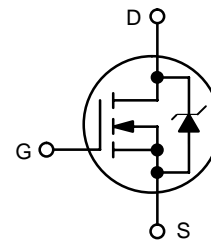
1. Surface-mounted on FR4 board using 1" sq. pad size (Cu area = 1.127" sq. [1 oz] including traces).
2. Surface-mounted on FR4 board using the minimum recommended pad size (Cu area = 0.412" sq.).



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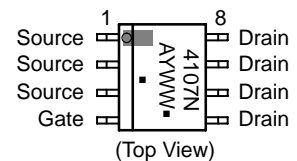
$V_{(BR)DSS}$	$R_{DS(on)}$ TYP	I_D MAX
30 V	3.4 m Ω @ 10 V	18 A
	4.7 m Ω @ 4.5 V	



MARKING DIAGRAM/ PIN ASSIGNMENT



SO-8
CASE 751
STYLE 12



4107N = Specific Device Code
 A = Assembly Location
 Y = Year
 WW = Work Week
 ■ = Pb-Free Package
 (Note: Microdot may be in either location)

ORDERING INFORMATION

Device	Package	Shipping†
NTMS4107NR2	SO-8	2500/Tape & Reel
NTMS4107NR2G	SO-8 (Pb-Free)	2500/Tape & Reel

†For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

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ELECTRICAL CHARACTERISTICS (T_J = 25°C unless otherwise noted)

Characteristic	Symbol	Test Condition	Min	Typ	Max	Unit
OFF CHARACTERISTICS						
Drain-to-Source Breakdown Voltage	V _{(BR)DSS}	V _{GS} = 0 V, I _D = 250 μA	30			V
Drain-to-Source Breakdown Voltage Temperature Coefficient	V _{(BR)DSS} /T _J			21		mV/°C
Zero Gate Voltage Drain Current	I _{DSS}	V _{GS} = 0 V, V _{DS} = 24 V	T _J = 25°C		1.0	μA
			T _J = 125°C		10	
Gate-to-Source Leakage Current	I _{GSS}	V _{DS} = 0 V, V _{GS} = ±20 V			±100	nA

ON CHARACTERISTICS (Note 3)

Gate Threshold Voltage	V _{GS(TH)}	V _{GS} = V _{DS} , I _D = 250 μA	1.0		2.5	V
Negative Threshold Temperature Coefficient	V _{GS(TH)} /T _J			7.4		mV/°C
Drain-to-Source On Resistance	R _{DS(on)}	V _{GS} = 4.5 V, I _D = 14 A		4.7	5.5	mΩ
		V _{GS} = 10 V, I _D = 15 A		3.4	4.5	
Forward Transconductance	g _{FS}	V _{DS} = 15 V, I _D = 18 A		25		S

CHARGES, CAPACITANCES AND GATE RESISTANCE

Input Capacitance	C _{ISS}	V _{GS} = 0 V, f = 1.0 MHz, V _{DS} = 15 V		6000		pF
Output Capacitance	C _{OSS}			1030		
Reverse Transfer Capacitance	C _{RSS}			550		
Total Gate Charge	Q _{G(TOT)}	V _{GS} = 4.5 V, V _{DS} = 15 V, I _D = 18 A		45		nC
Threshold Gate Charge	Q _{G(TH)}			6.5		
Gate-to-Source Charge	Q _{GS}			16.3		
Gate-to-Drain Charge	Q _{GD}			19.3		
Gate Resistance	R _G			0.60		

SWITCHING CHARACTERISTICS (Note 4)

Turn-On Delay Time	t _{d(ON)}	V _{GS} = 10 V, V _{DS} = 15 V, I _D = 1.0 A, R _G = 6.0 Ω		9.0		ns
Rise Time	t _r			10		
Turn-Off Delay Time	t _{d(OFF)}			94		
Fall Time	t _f			38		

DRAIN-SOURCE DIODE CHARACTERISTICS

Forward Diode Voltage	V _{SD}	V _{GS} = 0 V, I _S = 3.0 A	T _J = 25°C	0.8	1.1	V
			T _J = 125°C	0.6		
Reverse Recovery Time	t _{RR}	V _{GS} = 0 V, dI _S /dt = 100 A/μs, I _S = 3.0 A		41		ns
Charge Time	t _a			20		
Discharge Time	t _b			21		
Reverse Recovery Charge	Q _{RR}			48		

3. Pulse Test: Pulse Width ≤ 300 μs, Duty Cycle ≤ 2%.

4. Switching characteristics are independent of operating junction temperatures.

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TYPICAL PERFORMANCE CURVES

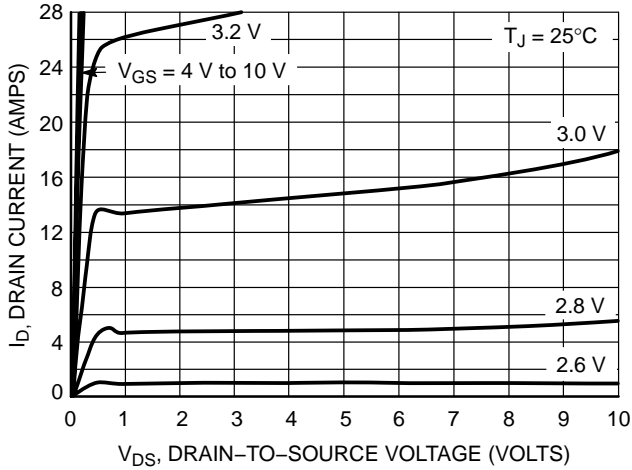


Figure 1. On-Region Characteristics

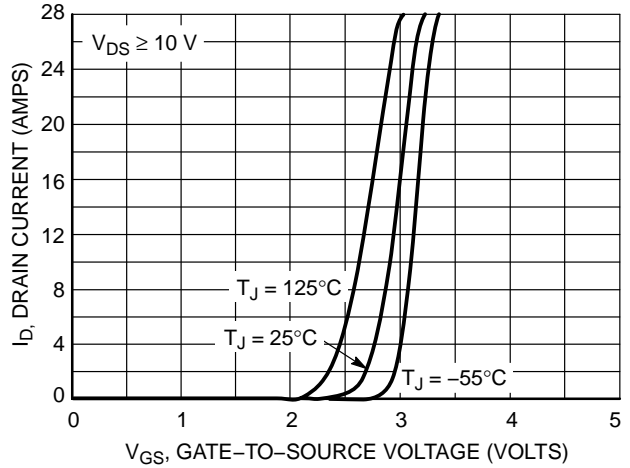


Figure 2. Transfer Characteristics

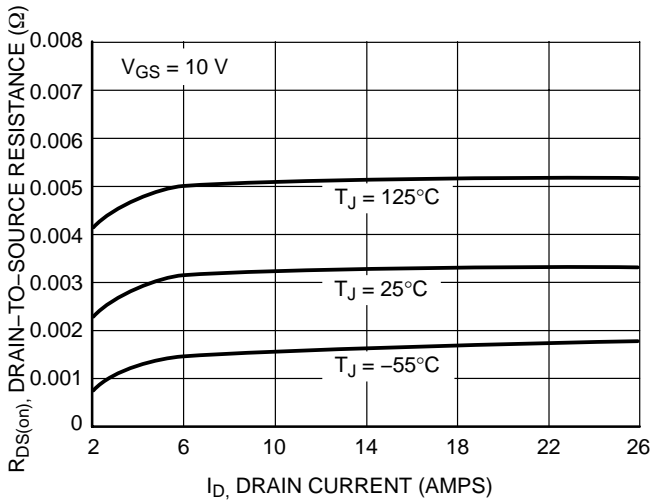


Figure 3. On-Resistance vs. Drain Current and Temperature

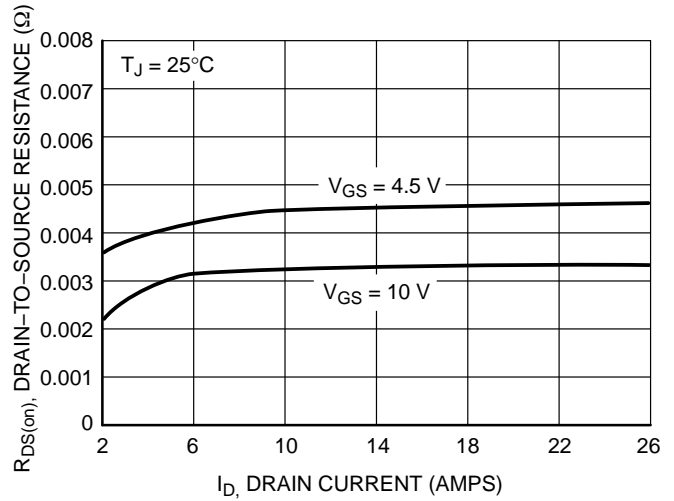


Figure 4. On-Resistance vs. Drain Current and Gate Voltage

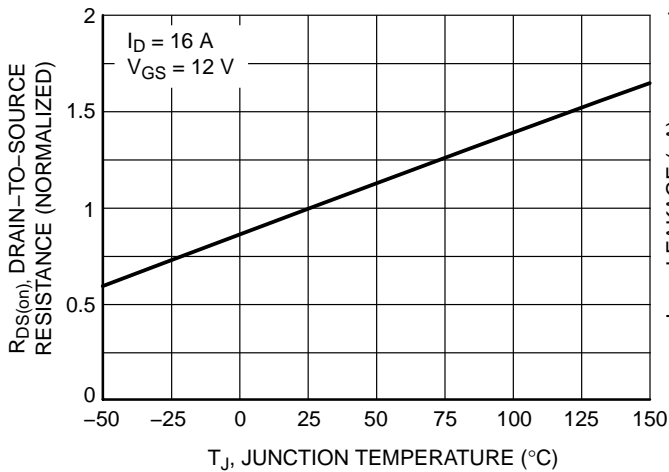


Figure 5. On-Resistance Variation with Temperature

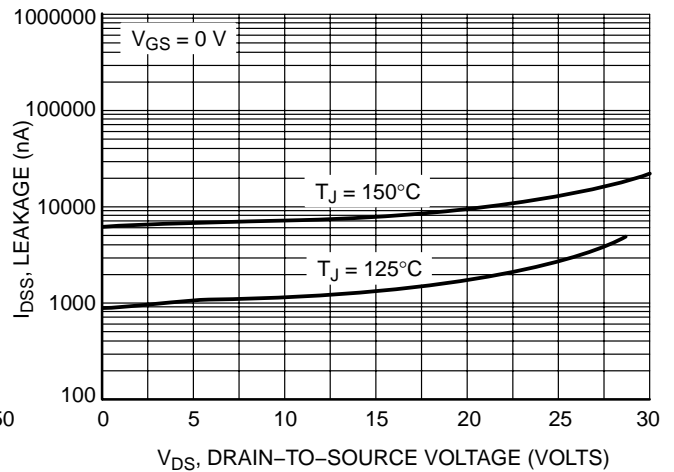


Figure 6. Drain-to-Source Leakage Current vs. Voltage

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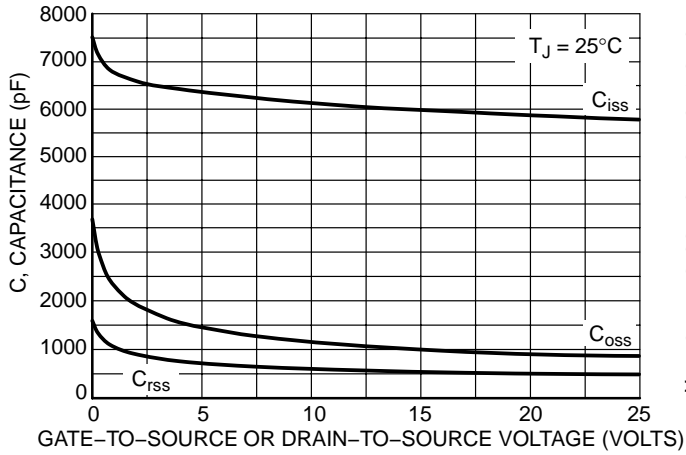


Figure 7. Capacitance Variation

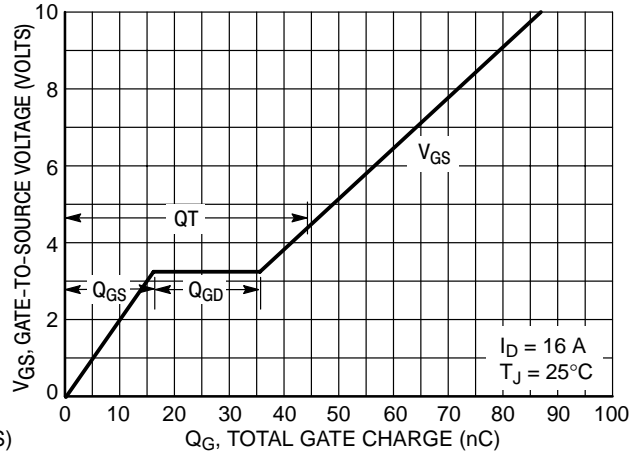


Figure 8. Gate-To-Source and Drain-To-Source Voltage vs. Total Charge

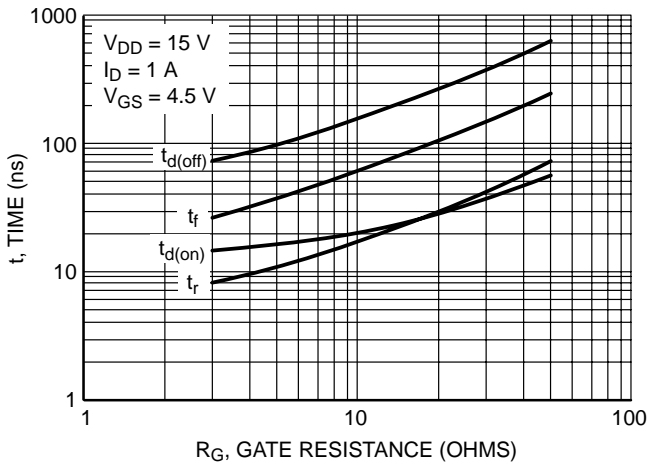


Figure 9. Resistive Switching Time Variation vs. Gate Resistance

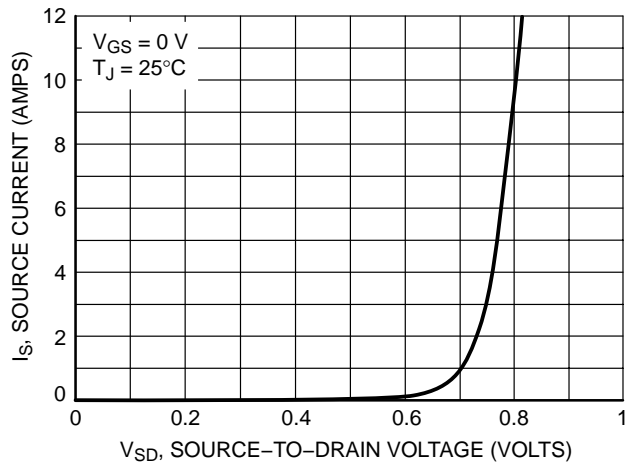


Figure 10. Diode Forward Voltage vs. Current

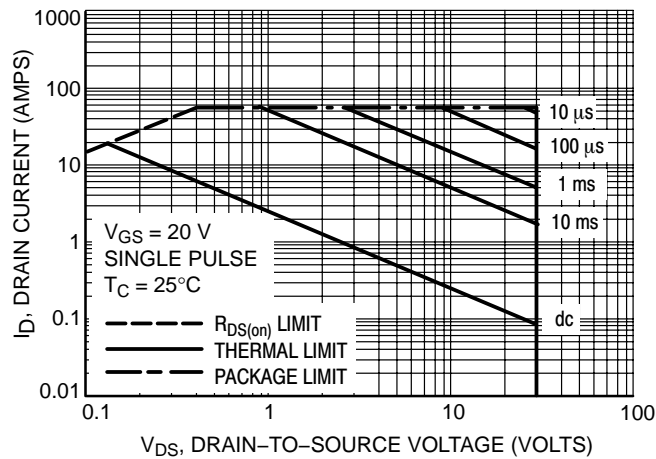


Figure 11. Maximum Rated Forward Biased Safe Operating Area

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